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APPLICANT : MITSUBISHI MATERIALS CORP;

INVENTOR : KINOSHITA MAKOTO;

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TITLE : SPUTTERING TARGET MATERIAL FOR FORMING THIN FILM OF THIN FILM TRANSISTOR

ABSTRACT : PURPOSE: To obtain a sputtering target material generating a small number of particles and capable of forming a thin film less liable to cause unevenness in the alloying component content with the lapse of time.

CONSTITUTION: This sputtering target material has a compsn. consisting of 1-20wt.% one or more kinds of alloying components selected from among Nb, V, Ti, Zr, Ni, Pt and W and the balance Al with inevitable impurities and a recrystallized structure contg. an intermetallic compd. of Al with the alloying components dispersed as particles of $\leq 30\mu\text{m}$ average particle diameter in the matrix of $\leq 30\mu\text{m}$ average grain diameter. This target material can suppress the generation of particles during film formation.

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